

Supplementary Materials: Synthesis, Properties and Aging of ICP-CVD SiC_xN_y:H Films Formed from Tetramethyldisilazane

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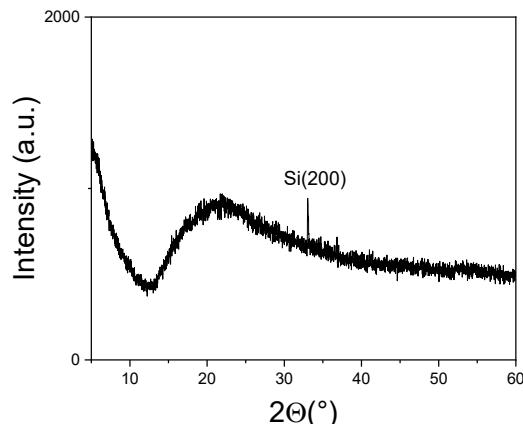


Figure S1. XRD pattern of SiC_xN_y film. The film deposition conditions: P(TMDSN)= 1×10^{-3} Torr, T_{dep}=200 °C, W=200 W, F(Ar) = 30 sccm, F(N₂) = 0 sccm.

Table S1. The surface free energy (surface tension) and its components for test liquids of different polarity (T = 25 ± 2 °C, P = 750 Torr) [1].

Liquid	E _d , mN/m	E _{IP} , mN/m	E _I , mN/m
Water	26.00	46.80	72.80 ± 0.05
Diethylene glycol	36 ± 2	9 ± 1	45.2 ± 0.4

References

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